

**METHOD FOR USING ASYMMETRIC OPC STRUCTURES ON LINE ENDS
OF SEMICONDUCTOR PATTERN LAYERS**

ABSTRACT

[0027] A method is disclosed for conducting optical proximity correction (OPC) on at least two features in a circuit design. After detecting a first feature having at least one end thereof to be in the proximity of one end of a second feature, a first OPC pattern is incorporated to the end of the first feature toward a first direction; and a second OPC pattern is incorporated to the end of the second feature toward a second direction that is substantially opposite from the first direction.